

Most Frequently Occurring Classifications of Patents Returned
From A Search of 10/660,559 on January 12, 2005

Combined Classifications

| | |
|---------------|---------------|
| 5 257/192 | 2 257/E29.14 |
| 5 257/E29.268 | 2 257/E29.175 |
| 4 257/488 | 2 257/E29.19 |
| 4 257/E21.387 | 2 257/E29.252 |
| 4 257/E21.625 | 2 257/E29.257 |
| 4 257/E21.639 | 2 257/E29.258 |
| 4 257/E29.114 | 2 257/E29.26 |
| 3 257/339 | 2 438/227 |
| 3 257/587 | 2 438/238 |
| 3 257/77 | 2 438/286 |
| 3 257/E21.375 | 2 438/297 |
| 3 257/E23.019 | 2 438/298 |
| 3 257/E29.051 | 2 438/305 |
| 3 257/E29.064 | 2 438/307 |
| 3 257/E29.185 | 2 438/384 |
| 3 257/E29.189 | |
| 3 257/E29.253 | |
| 3 257/E29.256 | |
| 3 438/586 | |
| 2 257/194 | |
| 2 257/197 | |
| 2 257/289 | |
| 2 257/290 | |
| 2 257/341 | |
| 2 257/344 | |
| 2 257/345 | |
| 2 257/399 | |
| 2 257/408 | |
| 2 257/409 | |
| 2 257/491 | |
| 2 257/495 | |
| 2 257/518 | |
| 2 257/577 | |
| 2 257/750 | |
| 2 257/758 | |
| 2 257/E21.086 | |
| 2 257/E21.167 | |
| 2 257/E21.407 | |
| 2 257/E21.418 | |
| 2 257/E21.419 | |
| 2 257/E21.576 | |
| 2 257/E21.593 | |
| 2 257/E21.696 | |
| 2 257/E23.164 | |
| 2 257/E27.012 | |
| 2 257/E29.01 | |
| 2 257/E29.013 | |
| 2 257/E29.03 | |
| 2 257/E29.104 | |
| 2 257/E29.124 | |

Titles of Most Frequently Occurring Classifications of Patents Returned
From A Search of 10/660,559 on January 12, 2005

- 5 257/192 (4 OR, 1 XR)
 - Class 257 : ACTIVE SOLID-STATE DEVICES
 - 257/183 HETEROJUNCTION DEVICE
 - 257/192 .Field effect transistor

- 4 257/488 (1 OR, 3 XR)
 - Class 257 : ACTIVE SOLID-STATE DEVICES
 - 257/487 WITH MEANS TO INCREASE BREAKDOWN VOLTAGE THRESHOLD
 - 257/488 .Field relief electrode

- 3 257/339 (1 OR, 2 XR)
 - Class 257 : ACTIVE SOLID-STATE DEVICES
 - 257/264 ...Enhancement mode or with high resistivity channel (e.g., doping of 10^{15} cm⁻³ or less)
 - 257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)
 - 257/327 ..Short channel insulated gate field effect transistor
 - 257/335 ...Active channel region has a graded dopant concentration decreasing with distance from source region (e.g., double diffused device, DMOS transistor)
 - 257/339With means to increase breakdown voltage

- 3 257/587 (0 OR, 3 XR)
 - Class 257 : ACTIVE SOLID-STATE DEVICES
 - 257/565 BIPOLAR TRANSISTOR STRUCTURE
 - 257/587 .With specified electrode means

- 3 257/77 (1 OR, 2 XR)
 - Class 257 : ACTIVE SOLID-STATE DEVICES
 - 257/76 SPECIFIED WIDE BAND GAP (1.5eV) SEMICONDUCTOR MATERIAL OTHER THAN GaAsP or GaAlAs
 - 257/77 .Diamond or silicon carbide

PLUS Search Results for S/N 10/660,559, Searched January 12, 2005 (Top 50)

The Patent Linguistics Utility System (PLUS) is a USPTO automated search system for U.S. Patents from 1971 to the present. PLUS is a query-by-example search system which produces a list of patents that are most closely related linguistically to the application searched. This search was prepared by the staff of the Scientific and Technical Information Center, SIRA.

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|---------|---------|---------|---------|---------|
| 5831292 | 5650658 | 4528744 | 4893157 | 5191402 |
| 4929991 | 5885878 | 4583105 | 4914491 | 5221856 |
| 4990990 | 5932894 | 4593152 | 4918026 | 5258631 |
| 5701026 | 5972759 | 4608696 | 4924288 | 5345101 |
| 5726069 | 6121684 | 4764801 | 4929992 | 5345103 |
| 6104043 | 4253105 | 4784968 | 4965650 | 5381027 |
| 6147371 | 4314269 | 4819044 | 4972237 | 5381031 |
| 5322804 | 4319257 | 4835592 | 4980748 | 5382814 |
| 5541435 | 4348746 | 4857479 | 5008719 | 5434435 |
| 5622878 | 4486770 | 4866491 | 5187122 | 5471232 |